

Physical-mechanical Properties of Ni-Doped Boron

G. Darsavelidze, O. Tsagareishvili, D. Gabunia, Z. Zoidze & L. Gabunia
F. Tavadze Institute of Metallurgy, Georgian Academy of Sciences, 380071, Tbilisi, Georgia

ABSTRACT. Temperature dependence of interval friction and shear modulus of boron-nickel alloys at 1Hz torsional oscillation in the temperature range from 300 to 1000 K has been investigated. In alloys with nickel content from 1.0 to 2.5% in the temperature range 450-500 K activation energy decreases from 1.25 to 0.8 eV and frequency factor changes from 5×10^9 to 1×10^{12} sec⁻¹. The origin of the maximum is explained by twin boundary migration in (100) plane. An additional maximum has been found in alloys with nickel content > 2.5% at 650 K with activation energy equal to 1.8eV and frequency factor about 10^{14} sec⁻¹. It is presumed that the variations of activation parameters of basic relaxation maximum of internal friction in nickel alloyed boron is caused by changes of electron contributions into migration activation energy of twin dislocations.

1. INTRODUCTION

In covalent crystals mobility of structural defect is determined to a large extent internal stresses and electrically active alloying elements (Jendrich and Haasen, 1988). The least investigated among such crystals, from the point of view of dislocation dynamics, is β -rhombohedral boron (below referred to as β -boron). Its structure is characterized by a large number of deformation twins and stacking faults (McKelvy, Smith and Fynng, 1982). In complex lattice structure β -boron variations of bond length, coordination number, dimensions and shapes of lattice holes where atoms of alloying elements can be inserted are encountered. Consequently electrical activity of solute atoms, nature of their influence on nucleation and migration of various structural defects can change depending on their valence and lattice position- As certain alloying elements have a strong effect on lattice parameters β -boron (Lundstrom, 1986), it is natural to expect ranges in crystallographic and activation characteristics of defects in alloyed boron.

It has been established (Gabunia and Tsomaia, 1974, Arifov, Panteleeva and Kantov, 1974) that

nickel in boron not only affects electrical and physical properties, but also changes the conductivity type. In this respect it is interesting to investigate the influence of nickel on electrical, physical and structural sensitive properties of β -boron.

In this paper results of research of electrical and physical properties, as well as temperature dependence of internal friction of nickel alloyed β -boron are presented. The aim of this investigation was to find connection between changes of structural sensitive properties of β -boron and on concentration and electrical activity of alloying elements.

2 METHOD AND MATERIAL

Samples have been obtained through melting of corresponding mixtures in boron nitride crucibles in a resistance furnace. The obtained samples had polycrystalline structure with irregular distribution of deformation twins and stacking faults in (100) plane. Boron alloys, containing 0.8... to 2.5 at % nickel, have been investigated. Electrical and physical properties of samples at room temperature have been investigated by fourprobe method in constant magnetic field. Temperature dependence of interval

friction and shear modulus have been studied at 1Hz torsional oscillations. It was shown (Table 1) that alloys containing up to 2.5 at % of nickel at room temperature are characterized by hole conductivity. Hole concentration varied from 10^{17} to 10^{18} cm⁻³, their mobility changed in 10^{-25} cm²V⁻¹sec⁻¹ range. Conductivity type inversion takes place in alloys containing more than 2.5 at % nickel. In such alloys concentration of electron carriers changes from 10^{19} to 10^{20} cm⁻³, while mobility decreases from 5 to 2.5 cm²V⁻¹sec⁻¹. Annealing in vacuum for 5h at 1000 K has no significant effect on electrical and physical properties of boron alloys containing up to 2.5 at% Ni.

In unalloyed boron at 1Hz torsional oscillation frequency intensive relaxation maximum has been found at about 530 K, accompanied by the shear modulus defect (≈ 0.5) (Fig 1). At 570 K a non-relaxation maximum of internal friction has been

observed. Above 600 K dynamic shear modulus is fully restored, that contradicts the behaviour of standard linear body" (Nowick and Berry, 1972).

Internal friction maximum at about 530 K is characterized by activation energy of 1.25eV (as determined by its temperature shift with frequency) and frequency factor of 5×10^{13} sec⁻¹. There was found no internal friction maximum at 570K in the studied alloys of B-Ni system (Fig 2). Temperature and activation characteristics of relaxation process at 530 K decrease as concentration of nickel increases (Table 2). In alloys with electron conductivity broad relaxation maximum was observed at about 650 K with intensity = 0.05 and modulus defect = 0.15. Relaxation process is characterized by activation energy 1.8eV and frequency factor 1×10^{14} sec⁻¹. Activation characteristics do not depend on nickel content in the range of studied alloy concentrations.

Table 1 Electrophysical characteristics of Ni-doped boron

Material	Conduction type	Charge carriers concentration cm ⁻³	Mobility of charge carriers, cm ² V ⁻¹ sec ⁻¹
B	P	$5 \cdot 10^{16}$	12
B+0.8at%Ni	P	10^{17}	20
B+1.7at%Ni	P	$3 \cdot 10^{18}$	25
B+2.5at%Ni	n	$2 \cdot 10^{20}$	5

Table 2 Physical-mechanical characteristics of Ni-doped boron

Material	Maximum temperature, K	Activation energy, eV	Frequency factor, sec ⁻¹	Shear modulus, GPa
B	530	1.25	$5 \cdot 10^{13}$	175
B+0.8at%Ni	510	1.10	$1 \cdot 10^{13}$	185
B+1.7at%Ni	490	1.05	$5 \cdot 10^{12}$	190
B+2.5at%Ni	475 650	0.80 1.80	$1 \cdot 10^{12}$ $1 \cdot 10^{14}$	200

Retaxation maximum intensity increases with the growth of deformation amplitudes while the maximum shifts by 10-20K to lower temperatures. These changes in alloys are similar to those in bcc metals and germanium crystals in which internal friction maximum connected with dislocations are observed (1). It is supposed, that intensive maximum at 530 K is connected with migration of twin boundaries by nucleation and expansion of twinning dislocation loops on (100) planes changes maximum at 650 K, found in alloys with n - type conductivity, might be connected with reversible of stacking width. Taking into account results of our research (Darsavehdze and Tsagareishvili, 1986) and specific peculiarities of dislocation migrations in alloyed semiconductors (Belavski, Dannski and Shalimov, 1982) we can interpret our results in the following way: at low stresses ($\sim 10^5$ G) activation energy of coherent twin boundary migration includes the energy of twin dislocation loop nucleation, migration energy of kinks along the twinning plane and, interaction energy of kinks with anchoring solutes. Nickel forms oxides, nitrides and carbides, that lower concentration of solute atoms around dislocations. Another explanation can be connected with electrically active solute atoms of nickel that can shift Fermi level near dislocations. As a result, concentration of electrons and holes in dislocation zones splitted by deformation fields of dislocation from the edges of volume zones (those of valence and conductivity) may change. Redistribution of charge comes in dislocation field conditions, at the expense of electron contribution, the decrease of the nucleation energy of kinks of twin dislocations.

Thus we may suppose, that the maximum of internal friction at 530K is conditioned by nucleation and expansion of twinning dislocation loops on (100) plane. Mechanism, explaining maximum at 650K may be connected with reversible changing of stacking fault width in twinning planes under the influence of oscillating stresses.

REFERENCES

- Anfov, U A, Panteleeva, G V, Kh Karuov, R. In Bor Poluchenie, struktura i svoystva Moskva, 1974,100-106
 Belavski, V J, Dannski, B M, Shalimov, V V Fizika tverdogo tela 29 I series 1982, 326-328 (Russian)
 Darsavehdze, G Sh, Tsagareishvili, O A, et al. Less-Common Metals, 117, 1986,189-193
 Gabunia, D L, Tsomaia, K P. In Bor Poluchenie, struktura i svoystva Moskva, 1974, 97-99 (Russian)
 Lendnich U, Haasen. P Physica Status Solidi (a). 108,1988,553-575
 Lundstrom, T In AIP Conference Proceedings New York. 1986,19-30
 McKelvy M J, Roe Smith AR Fyng L, Solid State Chemistry, 44,1982, 374-381
 Nowick, A.S. Berry, B S. Unified Relaxation in Crystalline Solids, Academic Press, New York and London, 1972,470

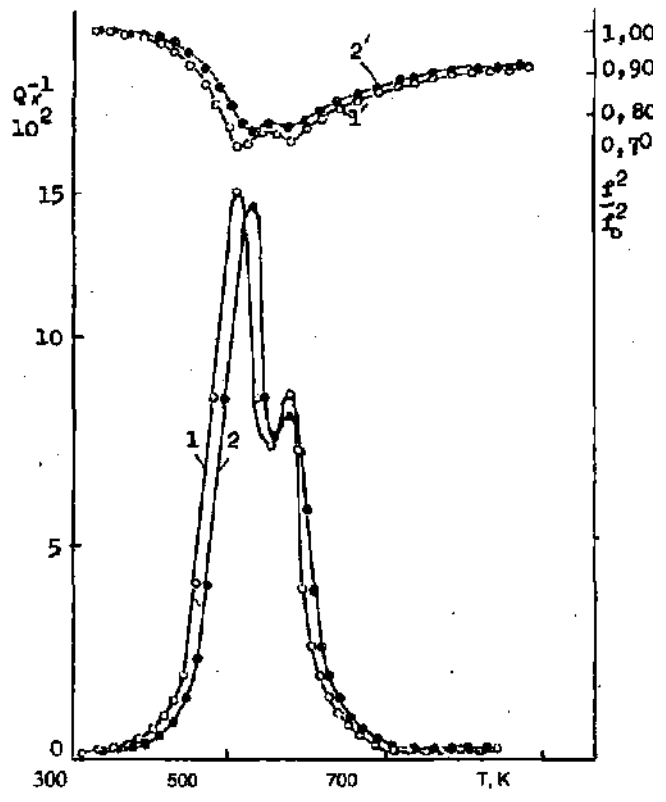


Figure I. Internal friction spectrum (Q^{-1}) and relative shear modulus (f^2/f_0^2) of polycrystalline β -boron.

- 1,1* - Q^{-1} and f^2/f_0^2 at the frequency $f_0=1\text{Hz}$
- 2,2' - Q^{-1} and f^2/f_0^2 at the frequency $f_0=5\text{Hz}$

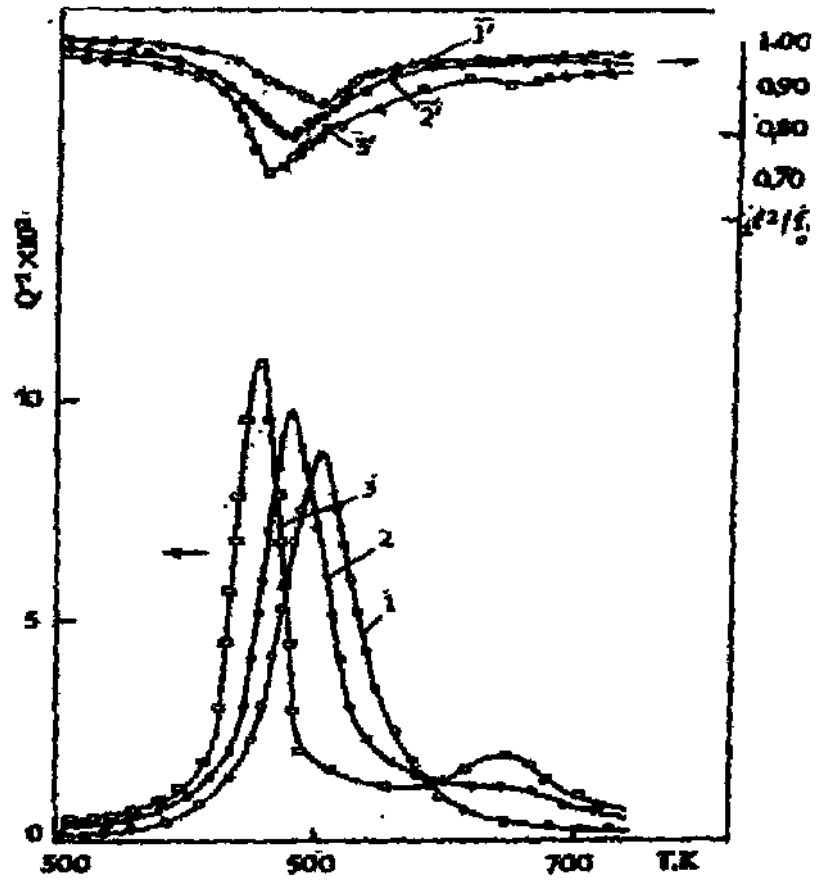


Figure 2 Internal friction spectrum(Q^{-1}) and relative shear modulus (f^2/f_0^2) of Ni-doped boron
 1, r - Q^{-1} and f^2/f_0^2 of B+0.8at%, Ni, $f_0=1$ Hz
 2, 2' - Q^{-1} and f^2/f_0^2 of B+1.7at %, Ni, $f_0=1$ Hz
 3, 3' - Q^{-1} and f^2/f_0^2 of B+2.5at %, Ni, $f_0=2$ Hz